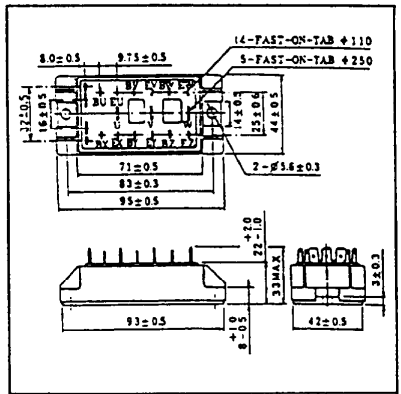


# MG25J6ES40

HIGH POWER SWITCHING APPLICATIONS.  
MOTOR CONTROL APPLICATIONS.

- The Electrodes are Isolated from Case.
- 6 IGBTs are Built Into 1 Package.
- Enhancement-Mode
- Low Saturation Voltage  
:  $V_{CE(sat)} = 3.5V$  (Max.) ( $I_C = 25A$ )
- High Speed:  $t_f = 0.35\mu s$  (Max.) ( $I_C = 25A$ )  
 $t_{rr} = 0.15\mu s$  (Max.) ( $I_F = 25A$ )

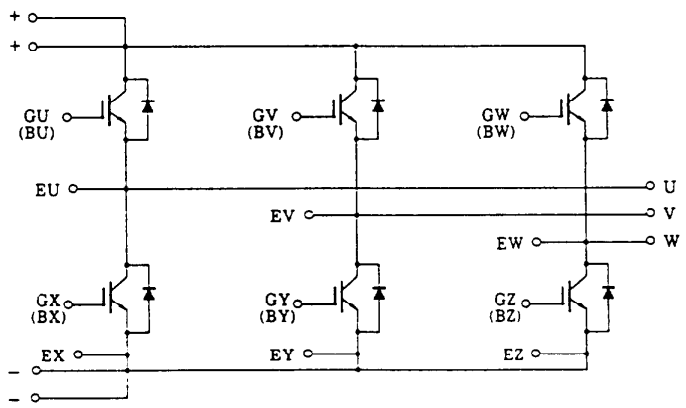
Unit in mm



JEDEC	—
EIAJ	—
TOSHIBA	2-72A5A

Weight : 225g

## EQUIVALENT CIRCUIT



# MG25J6ES40

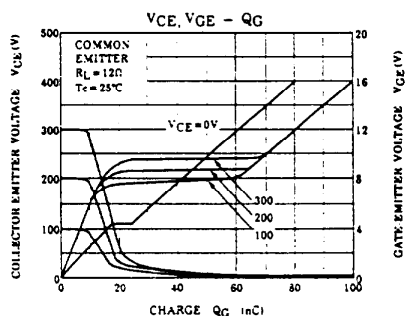
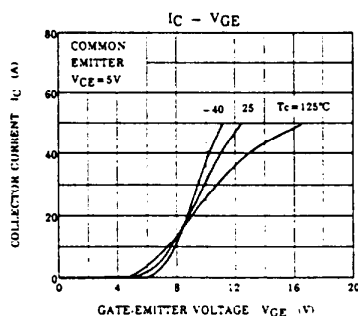
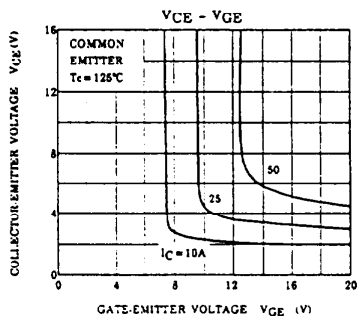
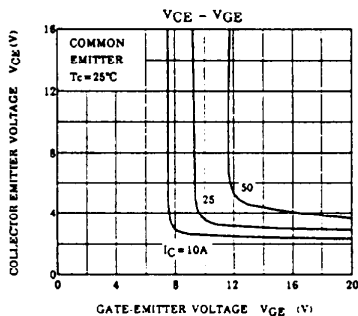
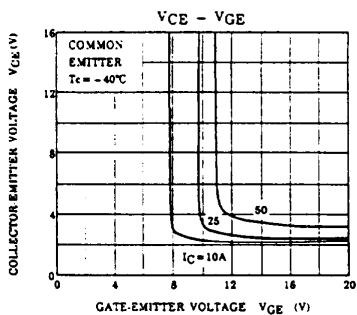
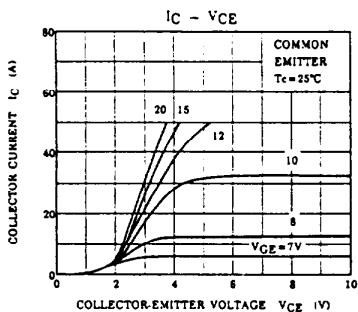
## MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Emitter Voltage	V <sub>CES</sub>	600	V
Gate-Emitter Voltage	V <sub>GES</sub>	±20	V
Collector Current	DC	I <sub>C</sub>	25
	1ms	I <sub>CP</sub>	50
Forward Current	DC	I <sub>F</sub>	25
	1ms	I <sub>FM</sub>	50
Collector Power Dissipation (Tc=25°C)	P <sub>C</sub>	100	W
Junction Temperature	T <sub>j</sub>	150	°C
Storage Temperature Range	T <sub>stg</sub>	-40~125	°C
Isolation Voltage	V <sub>Isol</sub>	2500 (AC, 1 min.)	V
Screw Torque	—	3	N·m

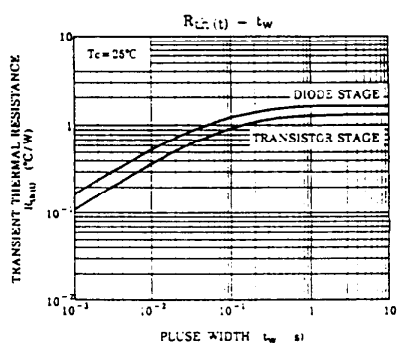
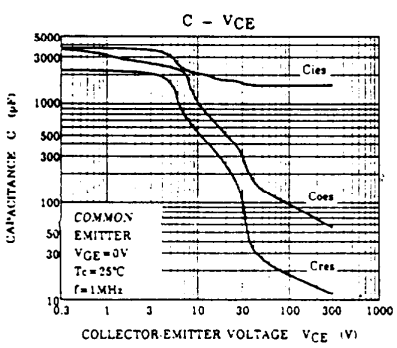
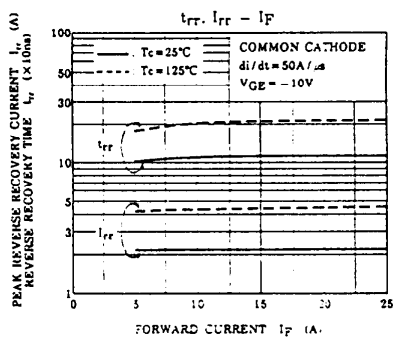
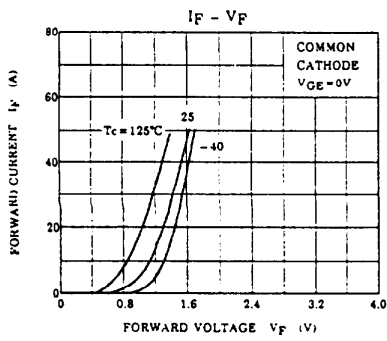
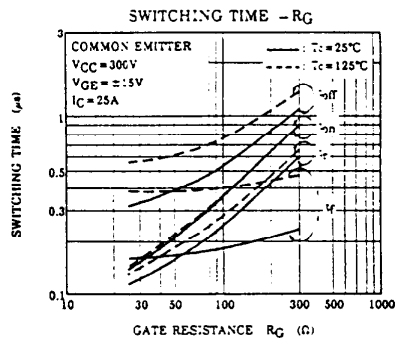
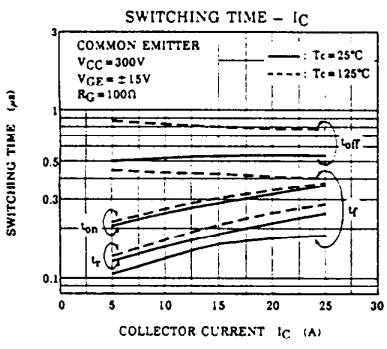
## ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT	
Gate Leakage Current	I <sub>GES</sub>	V <sub>GE</sub> = ±20V, V <sub>CE</sub> = 0	—	—	±500	nA	
Collector Cut-off Current	I <sub>CES</sub>	V <sub>CE</sub> = 600V, V <sub>GE</sub> = 0	—	—	1.0	mA	
Collector-Emitter Breakdown Voltage	V <sub>(BR)CES</sub>	I <sub>C</sub> = 10mA, V <sub>GE</sub> = 0	600	—	—	V	
Gate-Emitter Cut-off Voltage	V <sub>GE(off)</sub>	I <sub>C</sub> = 25mA, V <sub>CE</sub> = 5V	3.0	—	6.0	V	
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> = 25A, V <sub>GE</sub> = 15V	—	2.7	3.5	V	
Input Capacitance	C <sub>ies</sub>	V <sub>CE</sub> = 10V, V <sub>GE</sub> = 0, f = 1MHz	—	2000	—	pF	
Switching Time	Rise Time	t <sub>r</sub>		—	0.3	0.6	μs
	Turn-on Time	t <sub>on</sub>		—	0.4	0.8	
	Fall Time	t <sub>f</sub>		—	0.18	0.35	
	Turn-off Time	t <sub>off</sub>		—	0.60	1.0	
Forward Voltage	V <sub>F</sub>	I <sub>F</sub> = 25A, V <sub>GE</sub> = 0	—	1.7	2.5	V	
Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 25A, V <sub>GE</sub> = -10V di/dt = 50A/μs	—	0.08	0.15	μs	
Thermal Resistance	R <sub>th(j-c)</sub>	Transistor	—	—	1.25	°C/W	
		Diode	—	—	1.56		

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